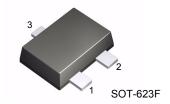


## **FJZ733**

### **Low Frequency Amplifier**

- Collector-Base Voltage : V<sub>CBO</sub>= -60V
  Complement to FJZ945



1. Base 2. Emitter 3. Collector

# **PNP Epitaxial Silicon Transistor**

## Absolute Maximum Ratings Ta=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>CBO</sub>	Collector-Base Voltage	-60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-50	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current	-150	mA
P <sub>C</sub>	Collector Power Dissipation	100	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

## **Electrical Characteristics** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = -100μA, I <sub>E</sub> =0	-60			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -10mA. I <sub>B</sub> =0	-50			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = -10\mu A. I_C = 0$	- 5			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =60V, I <sub>E</sub> =0			-100	nA
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = -5V, I <sub>C</sub> =0			-100	nA
h <sub>FE</sub>	DC Current Gain	$V_{CE}$ = -6V, $I_{C}$ = -1mA	40		700	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA		-0.18	-0.3	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE}$ = -6V, $I_{C}$ = -1mA	-0.50	-0.62	-0.80	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = -6V, I <sub>C</sub> = -10mA	50	180		MHz
C <sub>ob</sub>	Output Capacitance	$V_{CB}$ = -10V, $I_{E}$ = 0, f=1MHz		2.8		pF
NF	Noise Figure	$V_{CE}$ = -6V, $I_{C}$ = -0.3mA f=1MHz, Rs=10kΩ		6.0		dB

## Thermal Characteristics $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Max.	Units
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient	1250	°C/W

# $h_{\text{FE}}$ Classification & Marking

Classification	R	0	Y	G	L
h <sub>FE</sub>	40 ~ 80	70 ~ 140	120 ~ 240	200 ~ 400	350 ~ 700
Marking	A2	A3	A1	A4	A5



# **Typical Characteristics**

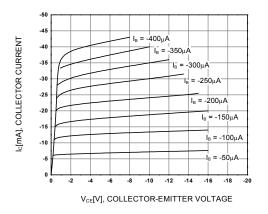


Figure 1. Static Characteristic

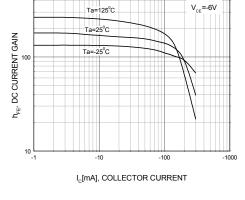


Figure 2. DC Current Gain

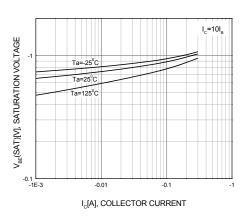


Figure 3. Base-Emitter Saturation Voltage

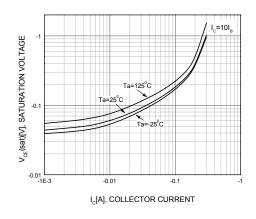


Figure 4. Collector-Emitter Saturation Voltage

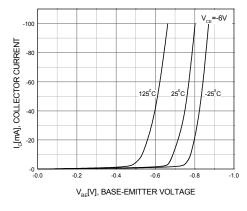


Figure 5. Base-Emitter On Voltage

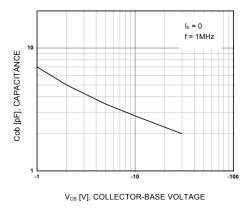


Figure 6. Collector Output Capacitance

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# Typical Characteristics (Continued)

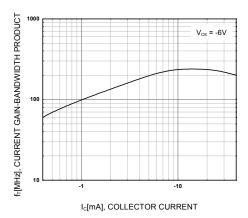
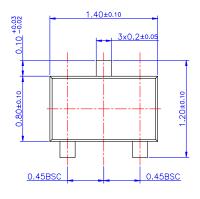
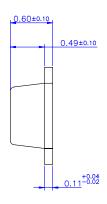


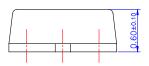
Figure 7. Current Gain Bandwidth Product

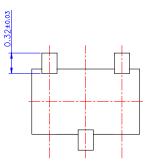
# **Package Dimensions**

# SOT-623F









Dimensions in Millimeters

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CoolFET™	FASTr™	MicroFET™	PowerTrench®	SuperSOT™-6
$CROSSVOLT^{\text{TM}}$	FRFET™	MicroPak™	QFET™	SuperSOT™-8
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E <sup>2</sup> CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	I <sup>2</sup> C™	OCX™	RapidConfigure™	UHC™
Across the board.	. Around the world.™	OCXPro™	RapidConnect™	UltraFET <sup>®</sup>
The Power Franchise™		OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	VCX™
Programmable Ad	ctive Droop™	OPTOPLANAR™	SMART START™	

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